Silicon PNP Power Transistors 2SB1362

DESCRIPTION

·With TO-3PN package
·Wide area of safe operation
·Complement to type 2SD2053

APPLICATIONS

·For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

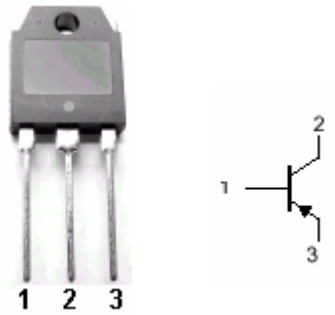

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-9	A
I_{CM}	Collector current -peak		-15	A
P_C	Collector power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-25mA; I_B=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-7A; I_B=-0.7A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-7A;V_{CE}=-5V			-1.8	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-50	μA
h_{FE-1}	DC current gain	I_C=-20mA ; V_{CE}=-5V	20			
h_{FE-2}	DC current gain	I_C=-1A ; V_{CE}=-5V	60		200	
h_{FE-3}	DC current gain	I_C=-7A ; V_{CE}=-5V	15			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-5V		15		MHz
C_{OB}	Collector output capacitance	f=1MHz;V_{CB}=-10V		270		pF

◆ **h_{FE-2} Classifications**

Q	P
60-120	100-200

PACKAGE OUTLINE

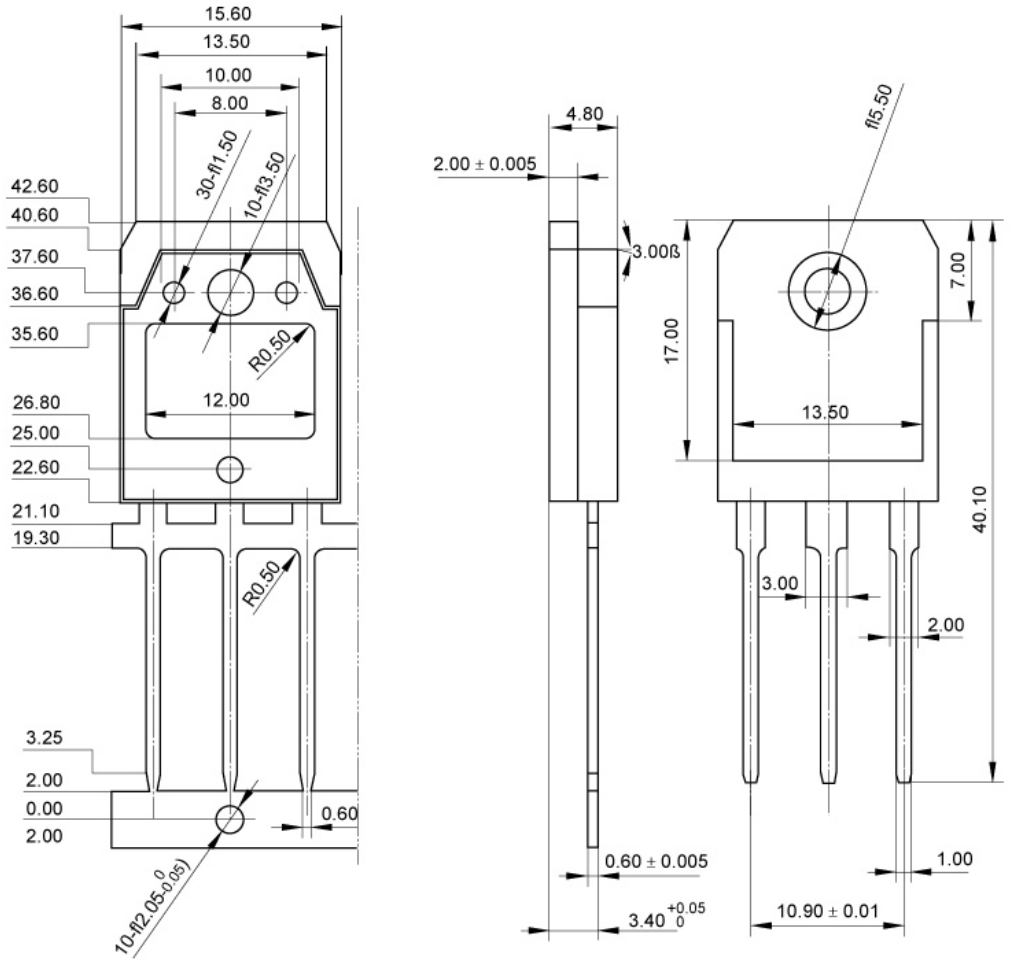

Fig.2 outline dimensions